

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A flip-chip-type gallium nitride compound semiconductor light-emitting device comprising a substrate, an n-type semiconductor layer, a light-emitting layer, and a p-type semiconductor layer,

wherein a negative electrode is provided on said n-type semiconductor layer, and a positive electrode is provided on said p-type semiconductor layer;

the n-type semiconductor layer, the light-emitting layer, and the p-type semiconductor layer being successively provided atop said substrate in this order and being composed of a gallium nitride compound semiconductor,

wherein said positive electrode has a three-layer structure comprising an ohmic electrode layer composed of rhodium which is in contact with said p-type semiconductor layer, an adhesion layer composed of titanium which is provided on said ohmic electrode layer and has a thickness of 1000 Å to 3,000 Å, and a bonding pad layer provided on said adhesion layer and being composed of a metal selected from the group consisting of gold, aluminum, nickel, and copper, or composed of an alloy containing at least one of these metals;

wherein the bonding pad layer is provided atop a portion of the ohmic electrode layer, wherein said portion is less than the entirety of the ohmic electrode layer, and ~~that~~wherein the adhesion layer has the same dimension as the bonding pad layer.

Claims 2-3. (canceled).

4. (previously presented): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1, wherein said ohmic electrode layer has a thickness of 100 Å to 3,000 Å.

5. (original): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 4, wherein said ohmic electrode layer has a thickness of 500 Å to 2,000 Å.

6. (previously presented): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1, wherein said bonding pad layer has a thickness of at least 1,000 Å.

7. (original): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 6, wherein said bonding pad layer has a thickness of 3,000 Å to 5,000 Å.

8. (previously presented): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1, wherein said bonding pad layer is composed of gold.

9. (currently amended): A positive electrode for use in a gallium nitride compound semiconductor light-emitting device, wherein said positive electrode has a three-layer structure

comprising an ohmic electrode layer composed of rhodium which is brought into contact with a p-type semiconductor layer of said gallium nitride compound semiconductor light-emitting device, an adhesion layer composed of titanium which is provided on said ohmic electrode layer and has a thickness of 1000 Å to 3,000 Å , and a bonding pad layer provided on said adhesion layer, said bonding pad layer being composed of a metal selected from the group consisting of gold, aluminum, nickel, and copper, or composed of an alloy containing at least one of these metals; wherein the bonding pad layer is provided atop a portion of the ohmic electrode layer, wherein said portion is less than the entirety of the ohmic electrode layer, and ~~that~~wherein the adhesion layer has the same dimension as the bonding pad layer.

Claims 10-11. (canceled).

12. (previously presented): A light-emitting diode comprising a flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1.

13. (canceled).